



# Thyristor \ Diode Module

$V_{RRM} = 2 \times 1600 \text{ V}$

$I_{TAV} = 320 \text{ A}$

$V_T = 1,06 \text{ V}$

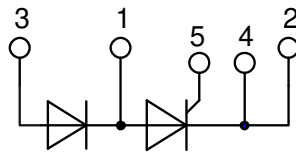
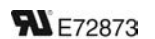
Phase leg

Part number

**MCD312-16io1**



Backside: isolated



### Features / Advantages:

- International standard package
- Direct copper bonded Al<sub>2</sub>O<sub>3</sub>-ceramic with copper base plate
- Planar passivated chip
- Keyed gate/cathode twin pins

### Applications:

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

### Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

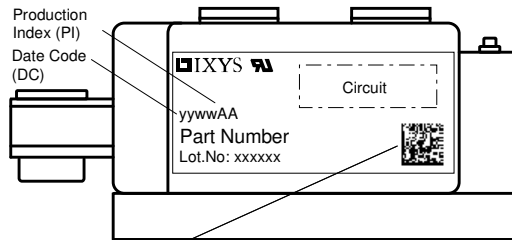
### Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).

Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1600	V
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1600 V$	$T_{VJ} = 25^{\circ}C$		1	mA
		$V_{R/D} = 1600 V$	$T_{VJ} = 140^{\circ}C$		40	mA
$V_T$	forward voltage drop	$I_T = 300 A$	$T_{VJ} = 25^{\circ}C$		1,12	V
		$I_T = 600 A$			1,32	V
		$I_T = 300 A$	$T_{VJ} = 125^{\circ}C$		1,06	V
		$I_T = 600 A$			1,29	V
$I_{TAV}$	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		320	A
$I_{T(RMS)}$	RMS forward current	180° sine			520	A
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0,80	V
$r_T$	slope resistance				0,68	mΩ
$R_{thJC}$	thermal resistance junction to case				0,12	K/W
$R_{thCH}$	thermal resistance case to heatsink			0,04		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		960	W
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		9,60	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		10,4	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		8,16	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		8,82	kA
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		460,8	kA <sup>2</sup> s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		447,4	kA <sup>2</sup> s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		332,9	kA <sup>2</sup> s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		323,3	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$	438		pF
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^{\circ}C$		120	W
		$t_p = 500 \mu s$			60	W
$P_{GAV}$	average gate power dissipation				20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 960 A$			100	A/μs
		$t_p = 200 \mu s; di_G/dt = 1 A/\mu s;$ $I_G = 1 A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 320 A$			500	A/μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	$T_{VJ} = 140^{\circ}C$		1000	V/μs
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		2	V
			$T_{VJ} = -40^{\circ}C$		3	V
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		150	mA
			$T_{VJ} = -40^{\circ}C$		220	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0,25	V
$I_{GD}$	gate non-trigger current				10	mA
$I_L$	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^{\circ}C$		200	mA
		$I_G = 0,45 A; di_G/dt = 0,45 A/\mu s$				
$I_H$	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		150	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 1 A; di_G/dt = 1 A/\mu s$				
$t_q$	turn-off time	$V_R = 100 V; I_T = 300 A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s; dv/dt = 50 V/\mu s; t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$	200		μs



Package Y1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			600	A
$T_{VJ}$	virtual junction temperature		-40		140	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				680		g
$M_D$	mounting torque		4,5		7	Nm
$M_T$	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	16,0			mm
$d_{Spb/Apb}$		terminal to backside	16,0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V



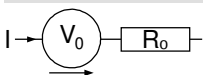
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD312-16io1	MCD312-16io1	Box	3	461857

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 140^{\circ}C$

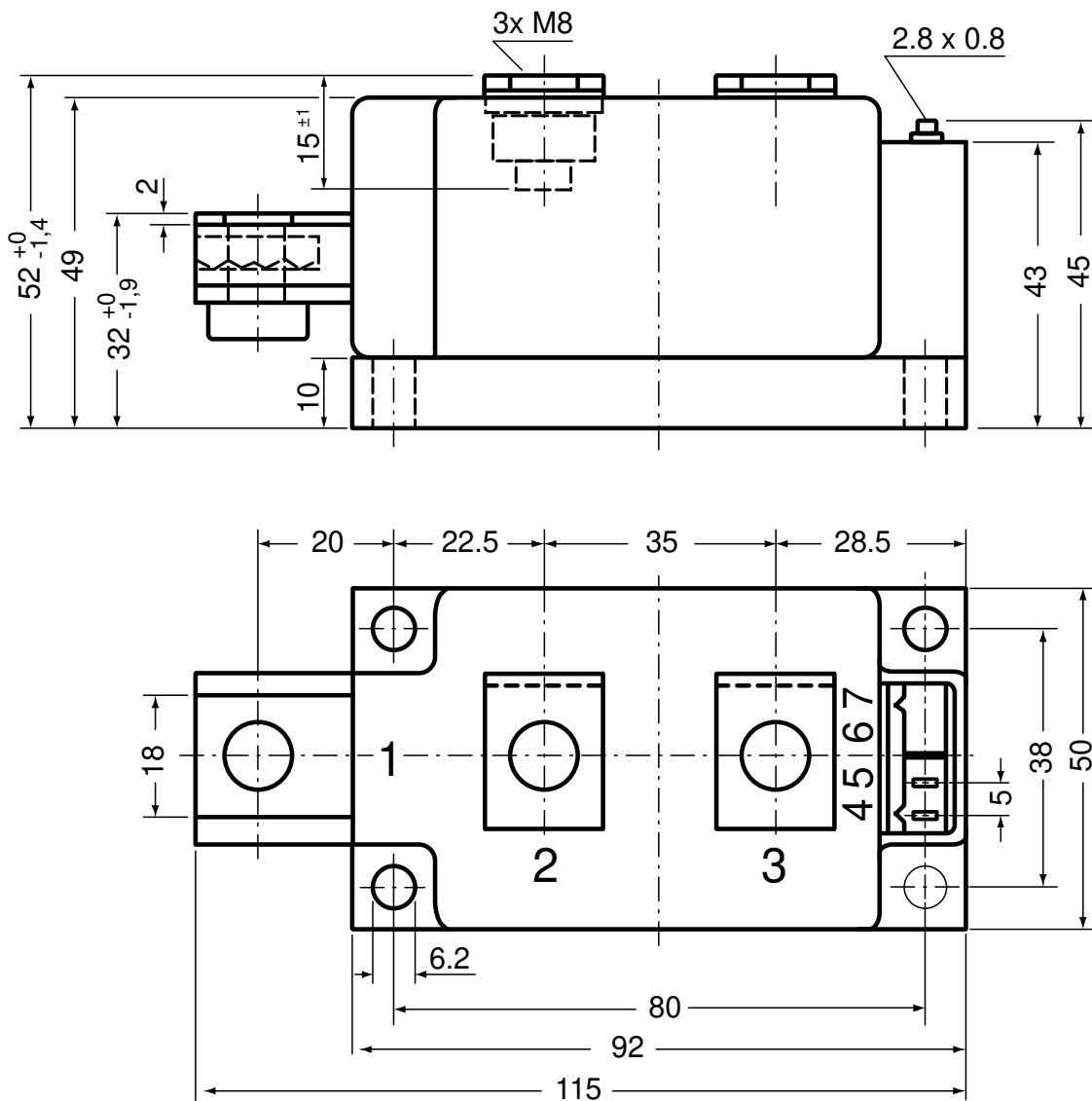


**Thyristor**

$V_{0\ max}$	threshold voltage	0,8	V
$R_{0\ max}$	slope resistance *	0,5	mΩ

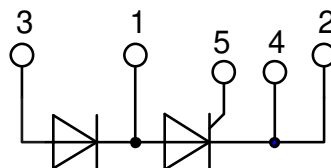


Outlines Y1



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red  
Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



**Thyristor**

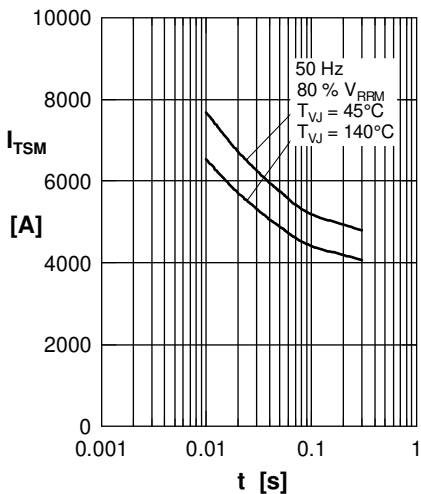


Fig. 1 Surge overload current  
 $I_{TSM}$ : Crest value,  $t$ : duration

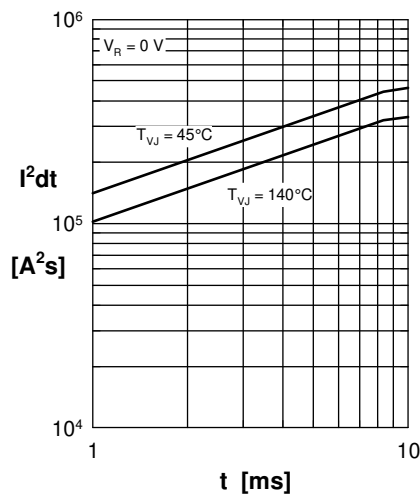


Fig. 2  $I^2dt$  versus time

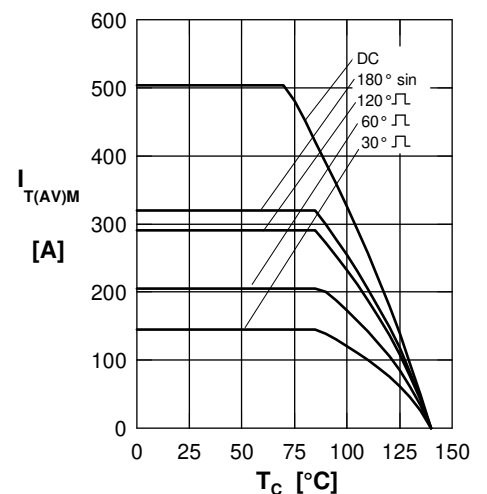


Fig. 3 Max. forward current at case temperature

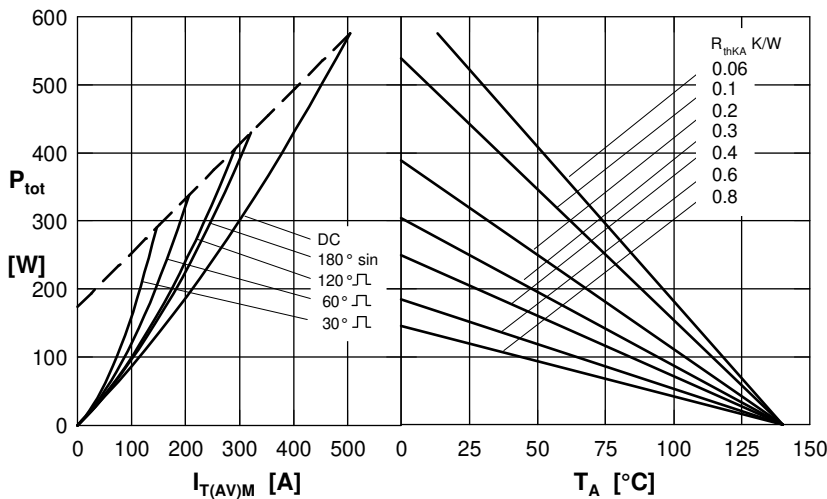


Fig. 4 Power dissipation versus on-state current and ambient temperature (per thyristor)

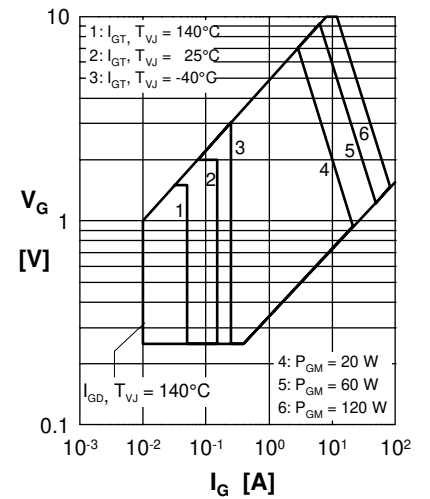


Fig. 5 Gate voltage & gate current

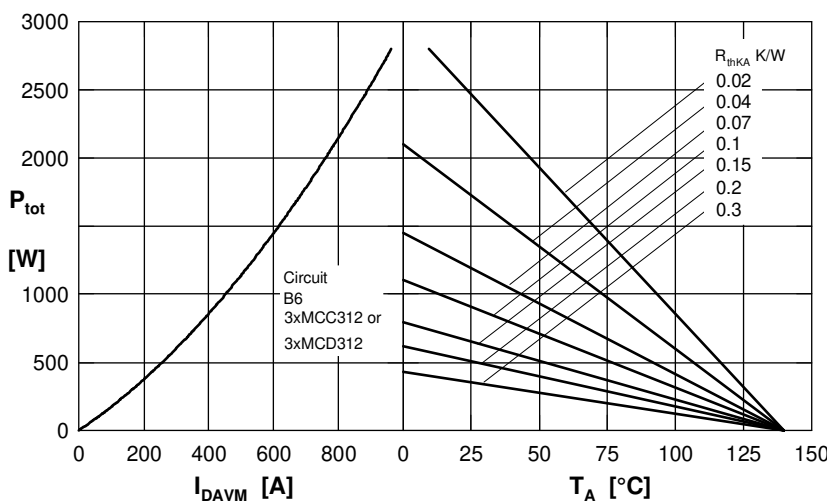


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

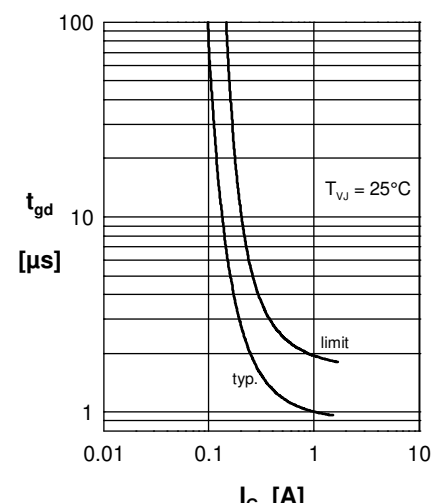


Fig. 7 Gate controlled delay time  $t_{gd}$



**Rectifier**

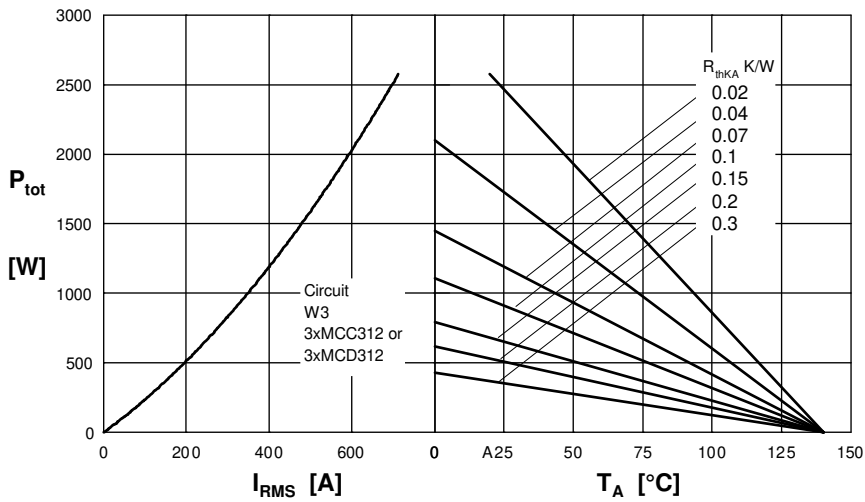


Fig. 8 Three phase AC-controller: Power dissipation versus  $R_{MS}$  output current and ambient temperature

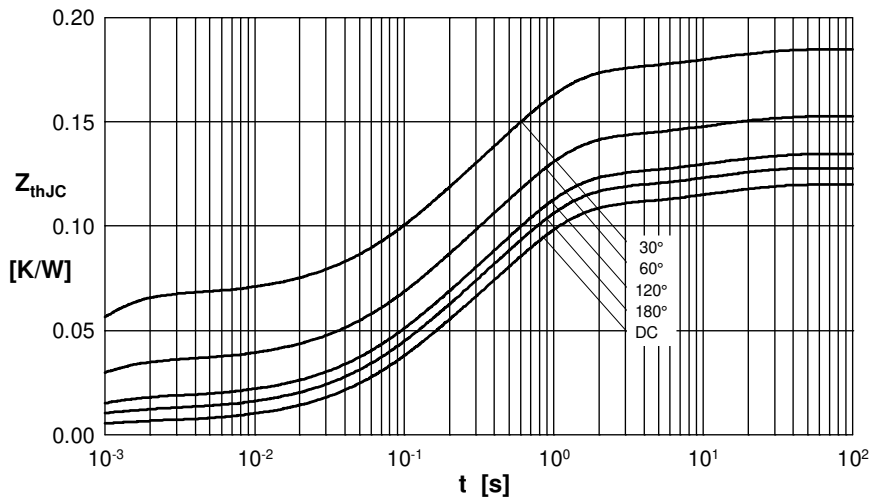


Fig. 9 Transient thermal impedance junction to case (per thyristor)

$R_{thjC}$  for various conduct. angles d:

d	$R_{thjC}$ [K/W]
DC	0.120
180°	0.128
120°	0.135
60°	0.153
30°	0.185

Constants for  $Z_{thjC}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0058	0.00054
2	0.0310	0.098
3	0.0720	0.54
4	0.0112	12

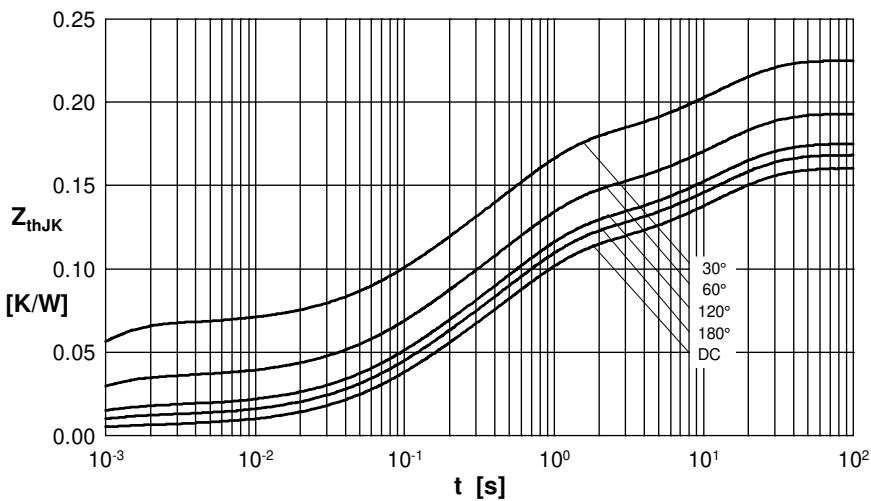


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

$R_{thjK}$  for various conduct. angles d:

d	$R_{thjK}$ [K/W]
DC	0.160
180°	0.168
120°	0.175
60°	0.193
30°	0.225

Constants for  $Z_{thjK}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0058	0.00054
2	0.0310	0.098
3	0.0720	0.54
4	0.0114	12
5	0.0400	12